

ESD Protection Array

Description

The usblc6-2sc6 is alow capacitance ESD Array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The usblc6-2sc6 has an ultra low capacitance with a typical value at 0.4pF, and complies with the IEC 61000-4-2 (ESD) standard with ±30kV air and ±25kV contact discharge. It is assembled into a 6-pin lead-free SOT23-6 package. The low capacitance array make it ideal for four high speed data and transmission line. This device is optimized for ESD protection of portable electronics.

Mechanical Characteristics

◆ Package: SOT23-6◆ Lead Finish: Matte Tin

◆ UL Flammability Classification Rating 94V-0

Case Material: "Green" Molding Compound
 Moisture Sensitivity: Level 3 per J-STD-020
 Terminal Connections: See Diagram Below

◆ Marking Information: See Below

Features

◆ Ultra low capacitance: 0.4pF typical (I/O to I/O)

Ultra low leakage: nA level

♦ Low operating voltage: 5V

Low clamping voltage

◆ 2 data lines and one power line protects

Complies with following standards:

- IEC 61000-4-2 (ESD) immunity test Air discharge: ±30kV

Contact discharge: ±25kV – IEC61000-4-4 (EFT) 40A (5/50ns)

- IEC61000-4-5 (Lightning) : 5A(8/20μs)

♦ ROHS Compliant

Applications

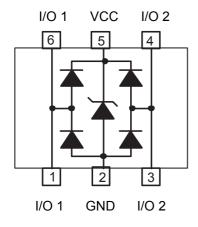
♦ USB 2.0 Ports

Digital video interface(DVI)

Monitor and Flat Panel Displays

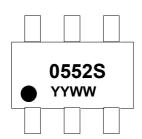
♦ Gigabit Ethernet

Dimensions and Pin Configuration



Circuit and Pin Schematic

Marking Information



0552S = Device Marking Code YYWW=Date Code Dot denotes Pin1



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

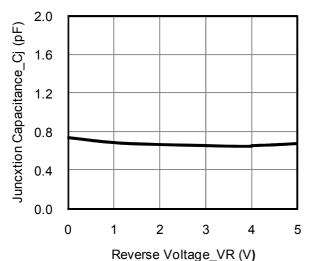
Parameter	Symbol	Value	Unit
Peak Pulse Power(tp=8/20µs)	Ррр	100	W
Peak Pulse Current (tp=8/20µs)	IPP	5	Α
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±30 ±25	kV
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

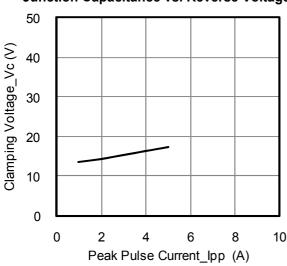
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6			٧	IT = 1mA
Reverse Leakage Current	I _R			0.5	μΑ	VRWM = 5V
Clamping Voltage	Vc			10	٧	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			20	V	IPP = 5A (8 x 20µs pulse)
Junction Capacitance	CJ		0.6	0.8	pF	VR = 0V, f = 1MHz, any I/O pin to ground
Junction Capacitance	CJ		0.3	0.4	pF	VR = 0V, f = 1MHz, between I/O pins

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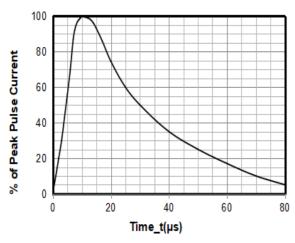
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



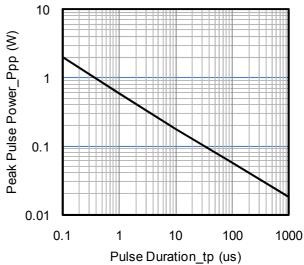
Junction Capacitance vs. Reverse Voltage



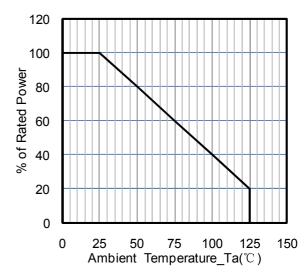
Clamping Voltage vs. Peak Pulse Current



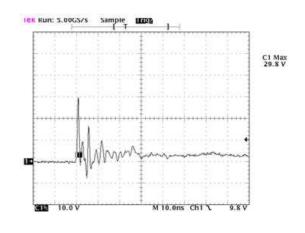
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



Power Derating Curve

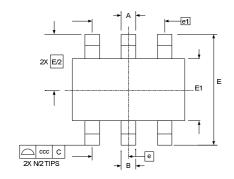


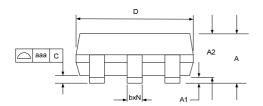
ESD Clamping Voltage 8 kV Contact per IEC61000-4-2



ESD Protection Array

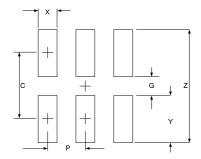
SOT23-6 Package Outline Drawing





	DIMENSIONS					
MILLIMETERS			INCHES			
SYM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90		1.45	0.035		0.057
A1	0.00		0.15	0.000		0.006
A2	0.90	1.15	1.30	0.035	0.045	0.051
b	0.25		0.50	0.010		0.020
С	0.08		0.22	0.003		0.009
D	2.80	2.90	3.10	0.110	0.114	0.122
E1	1.50	1.60	1.75	0.060	0.063	0.069
Е	2.80 BSC			0.110 BSC		
е	0.95 BSC			0.037 BSC		
e1	1.90 BSC			0.075 BSC		
N	6			6		
aaa	0.10			0.004		
ccc	0.20			0.008		

Suggested Land Pattern



SYM	DIMENSIONS				
	MILLIMETERS	INCHES			
С	2.50	0.098			
G	1.40	0.055			
Р	0.95	0.037			
Х	0.60	0.024			
Y	1.10	0.043			
Z	3.60	0.141			